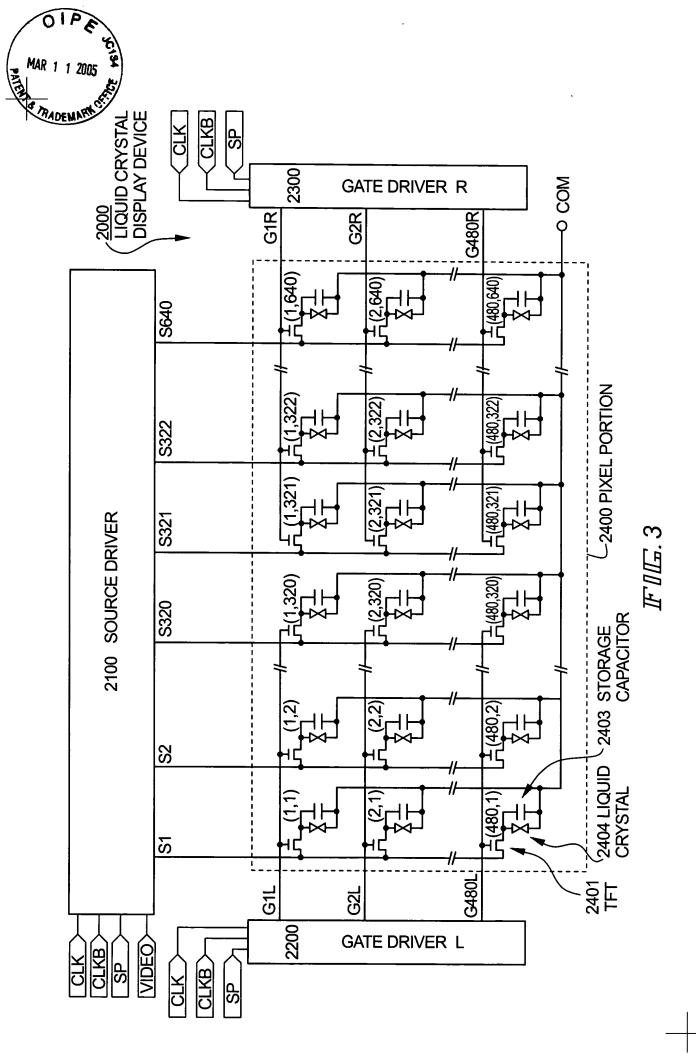


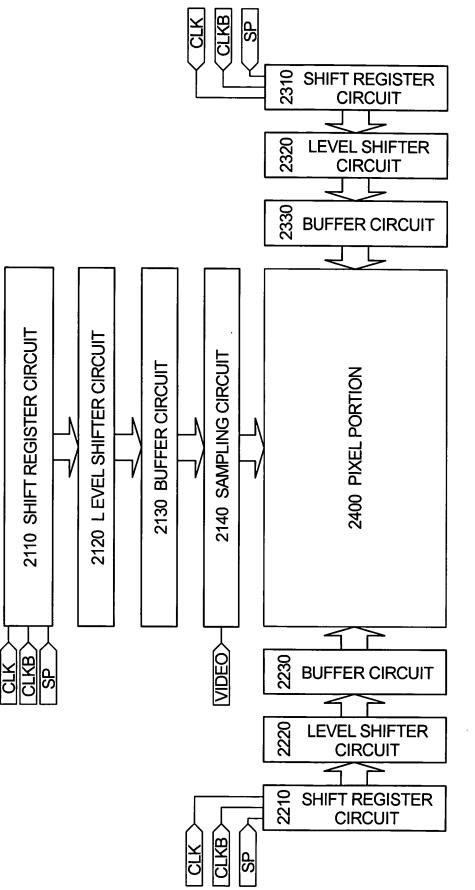


			-				NAL	(1,1)(1,2)	(1,1)	(1,2)			
FRAME PERIOD TF	LINE PERIOD TL HALF LINE PERIOD THL THL THL	G1L — SELECTION SIGNAL SELECTION SIGNAL SELECTION SIGNAL	G2L SELECTION SIGNAL	G2R SELECTION SIGNAL	G3 SELECTION SIGNAL	G4L SELECTION SIGNAL	G4R SELECTION SIGNAL	VIDEO - <u>(1,1)(1,2)(1,3)(1,4)(2,1)(2,3)(2,4)(3,1)(3,2)(3,3)(3,4)(4,1)(4,2)(4,3)(4,4)</u>	S1 - \(\(\frac{1}{1} \right) \(\frac{2}{1} \right) \(\frac{3}{1} \right) \(\frac{3}{1} \right) \(\frac{1}{1} \right) \(\frac{1} \right) \(\frac{1} \right) \(\frac{1}{1} \right) \(\frac{1}{1} \right	S2(1,2)(2,2)(3,2)(4,2)	S3(4,3)(2,3)(4,3)(4,3)	S4	IF ULE. 2

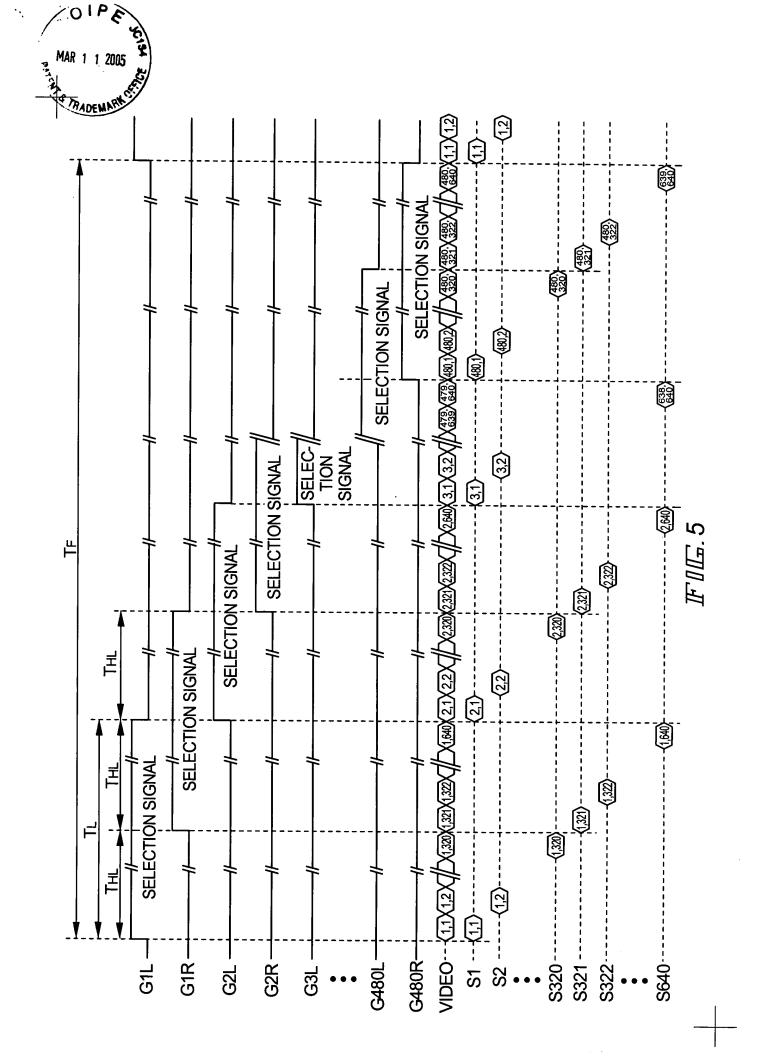


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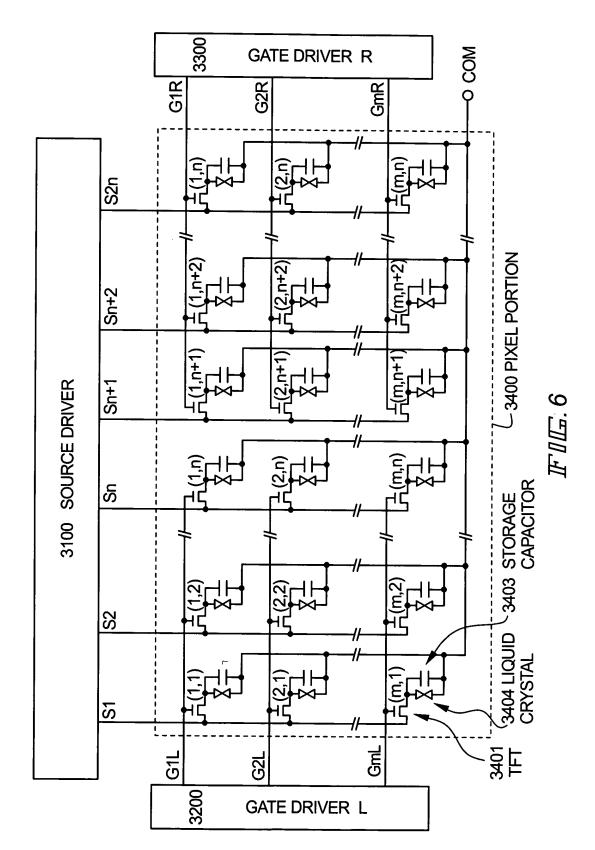


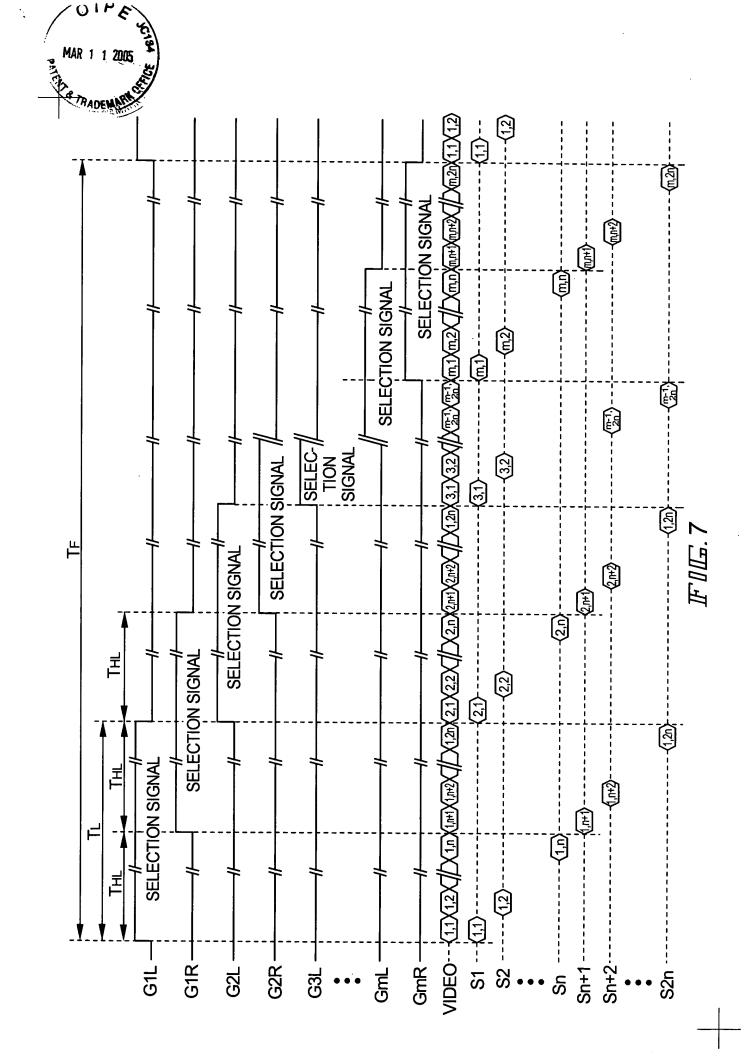
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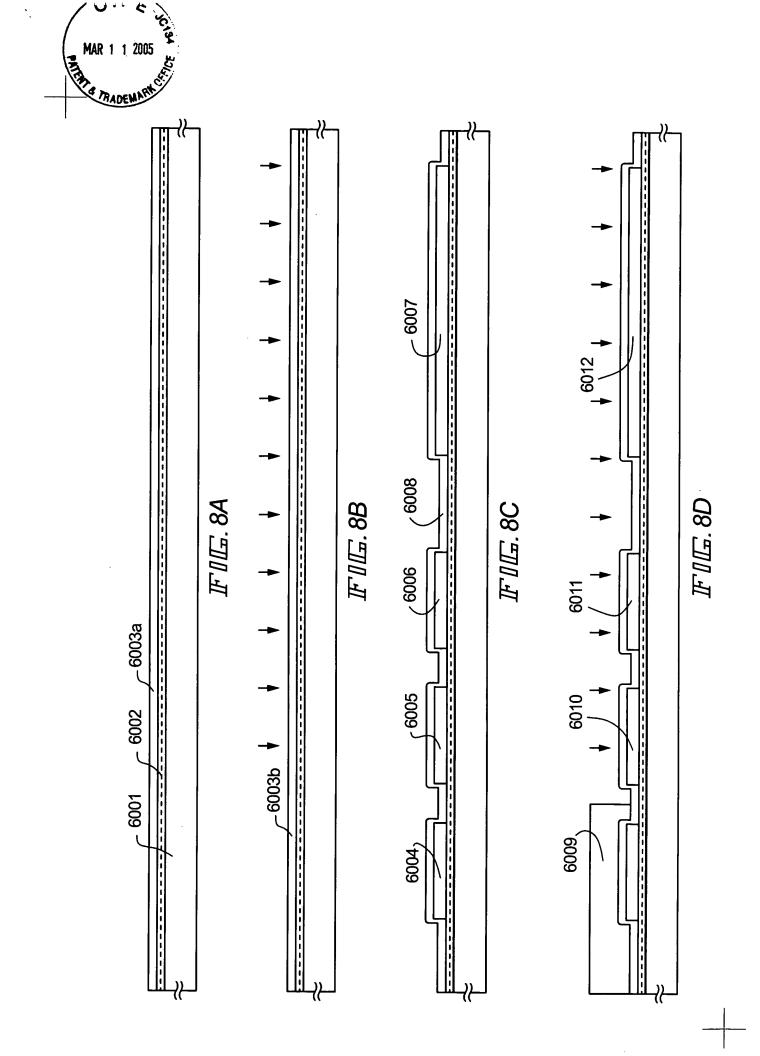


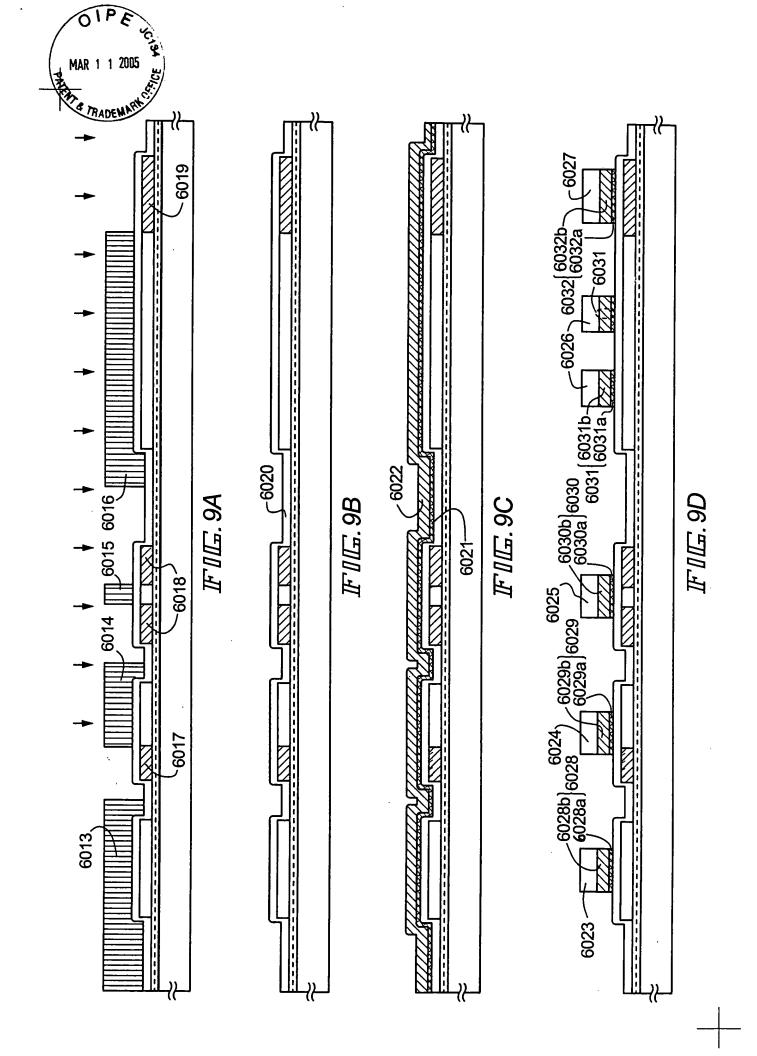
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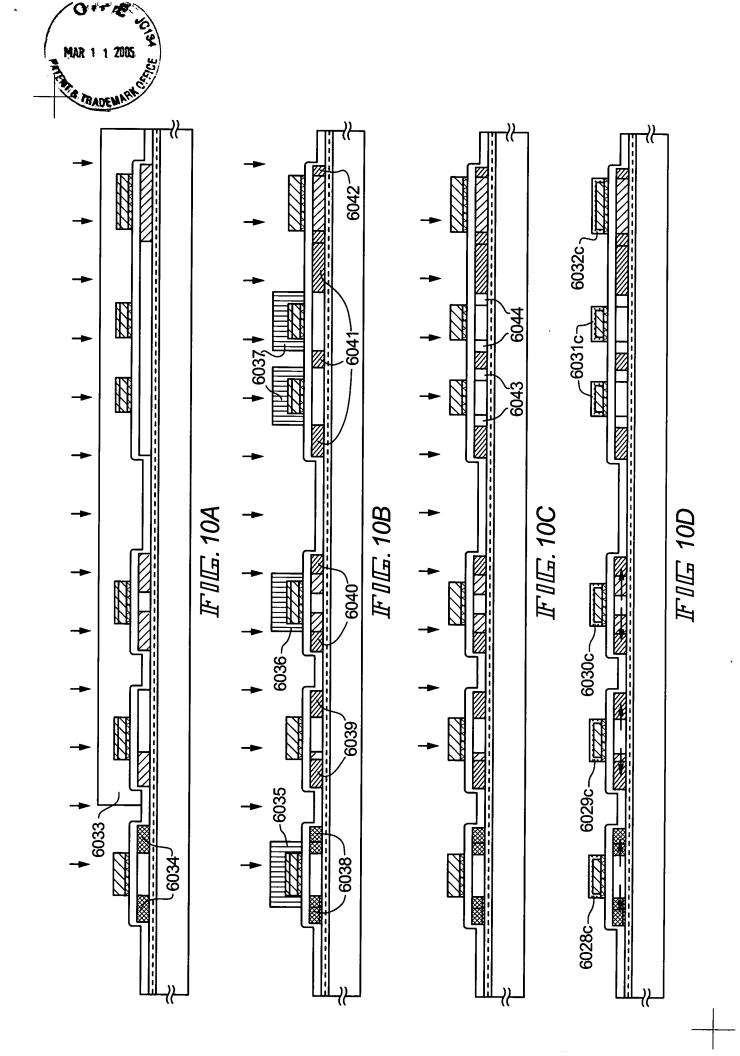


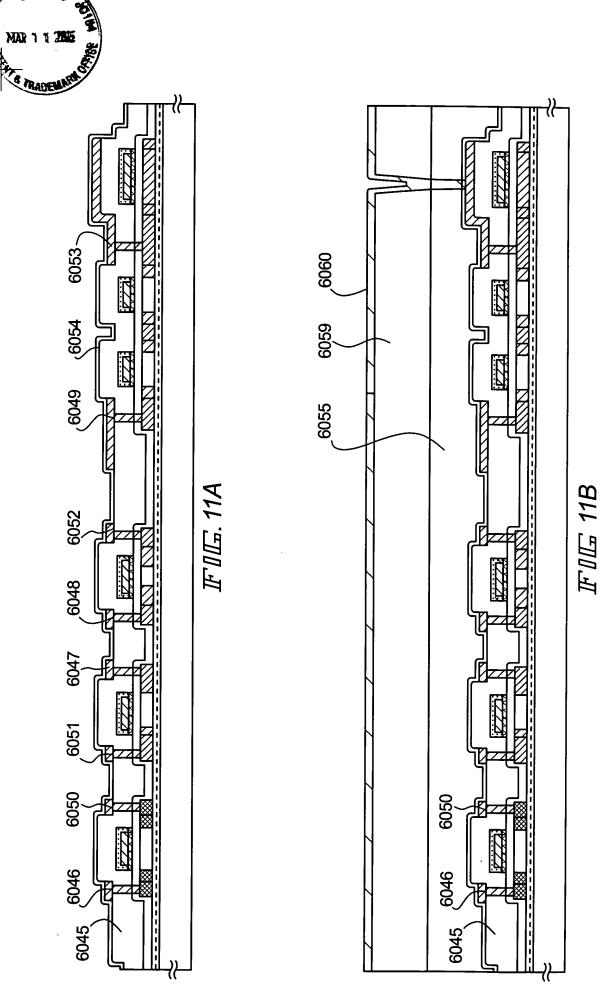


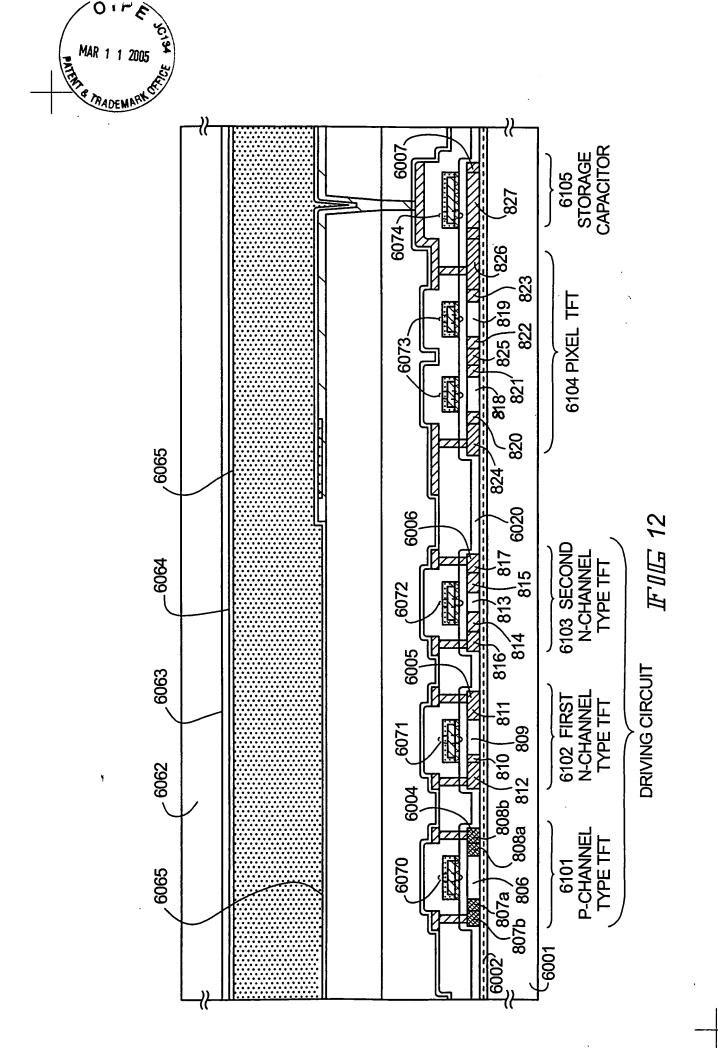






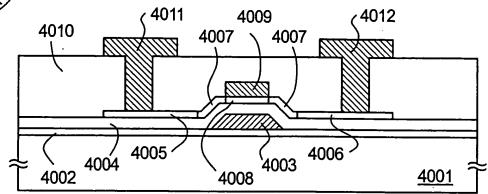






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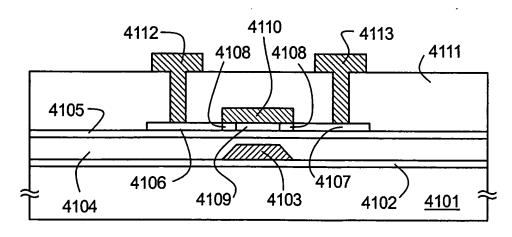




4001 SUBSTRATE
4002 SILICON OXIDE FILM
4003 GATE ELECTRODE
4004 GATE INSULATING FILM
4005 SOURCE REGION
4006 DRAIN REGION

4007 LOW CONCENTRATION IMPURITY REGION(LDD REGION) 4008 CHANNEL FORMING REGION 4009 CHANNEL PROTECTING FILM 4010 INTERLAYER INSULATING FILM 4011 SOURCE ELECTRODE 4012 DRAIN ELECTRODE

IF II III. 13A

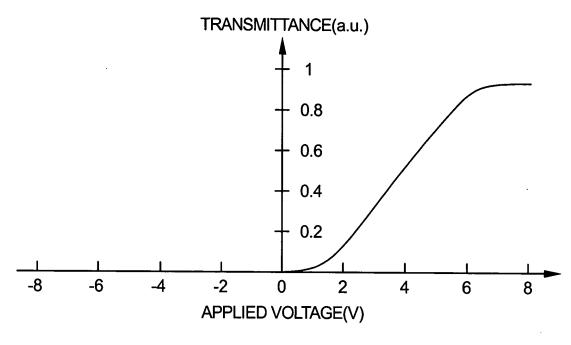


4101 SUBSTRATE
4102 SILICON OXIDE FILM
4103 GATE ELECTRODE
4104 BEIZOCYCLOBUTENE(BCB)
4105 SILICON NITRIDE FILM
4106 SOURCE REGION
4107 DRAIN REGION

4108 LOW CONCENTRATION
IMPURITY REGION(LDD REGION)
4109 CHANNEL FORMING REGION
4110 CHANNEL PROTECTING FILM
4111 INTERLAYER INSULATING FILM
4112 SOURCE ELECTRODE
4113 DRAIN ELECTRODE

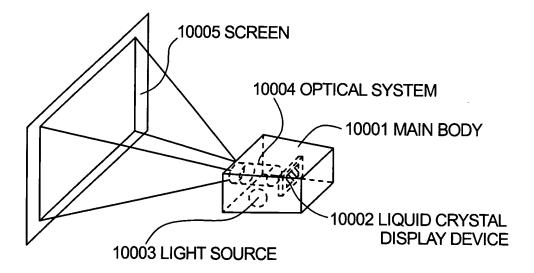
F[[压.13B]



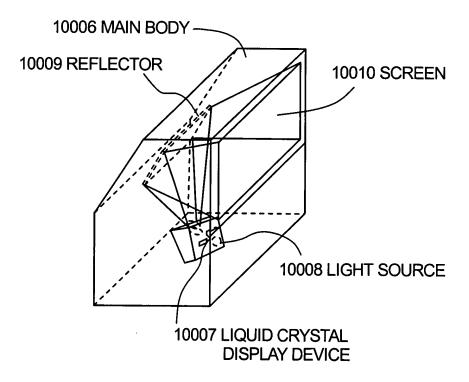


F0压.14





IF [[□]. 15A



IF [[压. 15B

